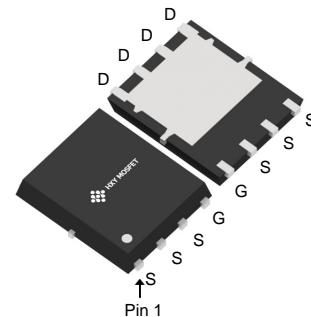




Description

The BSC059N03S G uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



DFN5X6-8L

General Features

$V_{DS} = 30V$ $I_D = 80A$

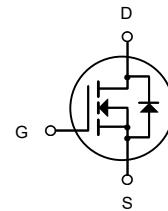
$R_{DS(ON)} < 6m\Omega$ $V_{GS} = 10V$

Application

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

Ordering Information

Product ID	Pack	Brand	Qty(PCS)
BSC059N03S G	DFN5X6-8L	HXY MOSFET	5000

Absolute Maximum Ratings ($T_c=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_c=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	80	A
$I_D @ T_c=70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	45	A
I_{DM}	Pulsed Drain Current	280	A
EAS	Single Pulse Avalanche Energy	56	mJ
$P_D @ T_c=25^\circ C$	Total Power Dissipation	37	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	30	°C/W



Electrical Characteristics @ $T_j=25^\circ\text{C}$ (unless otherwise specified)

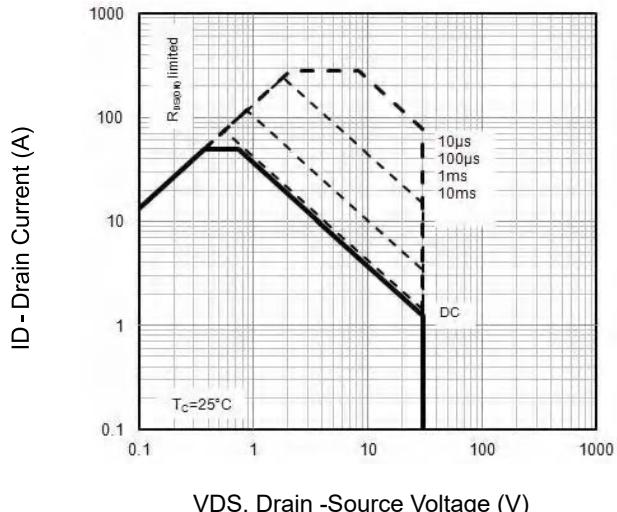
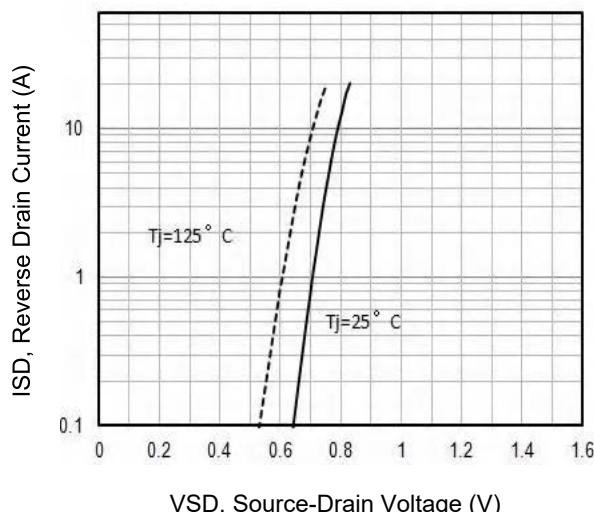
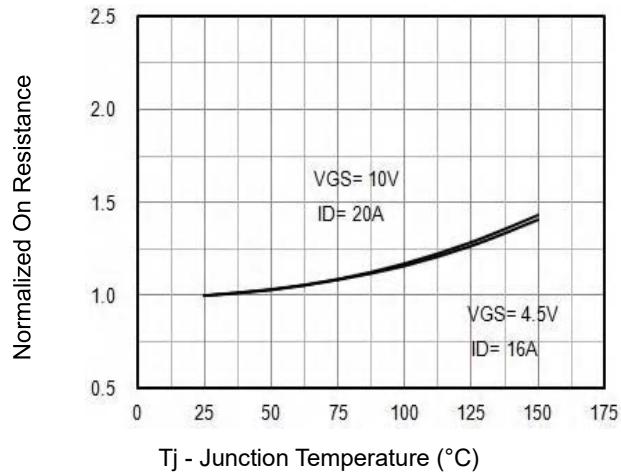
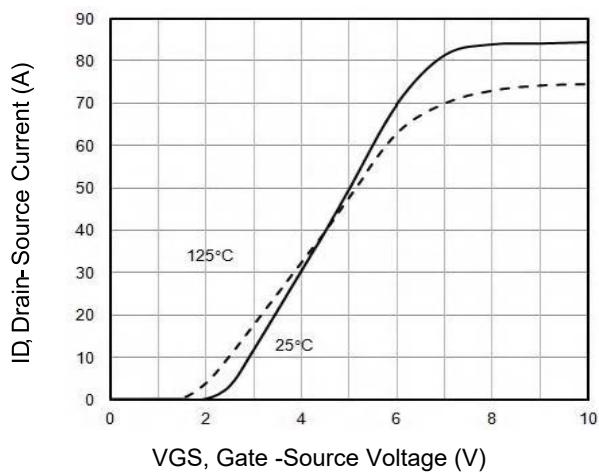
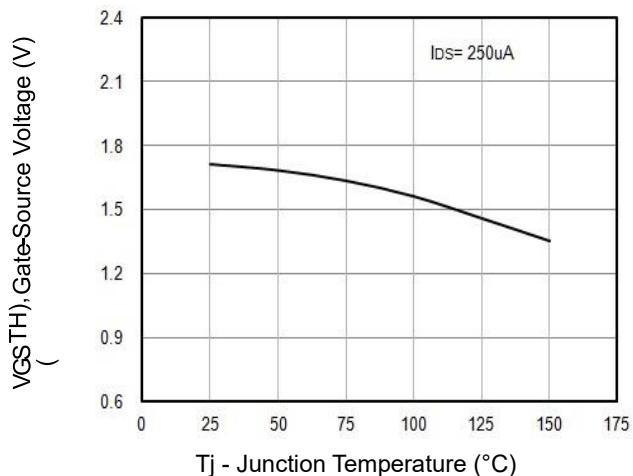
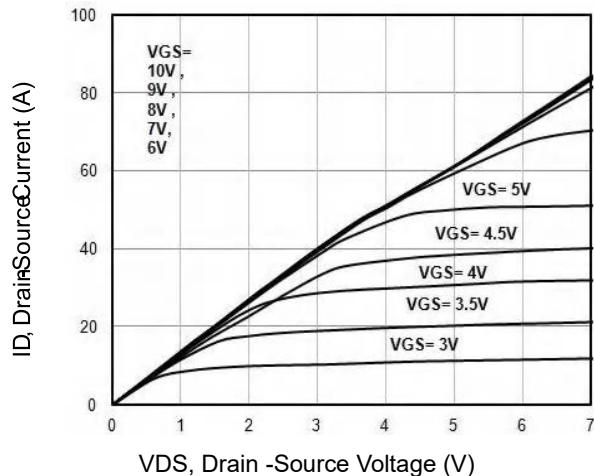
Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
Static Electrical Characteristics						
$V_{(\text{BR})\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}$ $I_{\text{D}}=250\mu\text{A}$	30	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{\text{DS}}=30\text{V}$, $V_{\text{GS}}=0\text{V}$	--	--	0.1	μA
	Zero Gate Voltage Drain Current($T_j=125^\circ\text{C}$)	$V_{\text{DS}}=30\text{V}$, $V_{\text{GS}}=0\text{V}$	--	--	100	μA
I_{GSS}	Gate-Body Leakage Current	$V_{\text{GS}}=\pm 20\text{V}$, $V_{\text{DS}}=0\text{V}$	--	--	± 100	nA
$V_{\text{GS}(\text{TH})}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}$, $I_{\text{D}}=250\mu\text{A}$	1.0	1.7	2.5	V
$R_{\text{DS}(\text{ON})}$	Drain-Source On-State Resistance ^③	$V_{\text{GS}}=10\text{V}$, $I_{\text{D}}=20\text{A}$	--	4.7	6	$\text{m}\Omega$
$R_{\text{DS}(\text{ON})}$	Drain-Source On-State Resistance ^③	$V_{\text{GS}}=4.5\text{V}$, $I_{\text{D}}=16\text{A}$	--	5.4	8	$\text{m}\Omega$
Dynamic Electrical Characteristics						
C_{iss}	Input Capacitance	$V_{\text{DS}}=15\text{V}$, $V_{\text{GS}}=0\text{V}$, $f=1\text{MHz}$	--	1930	--	pF
C_{oss}	Output Capacitance		--	310	--	pF
C_{rss}	Reverse Transfer Capacitance		--	260	--	pF
R_g	Gate Resistance	$f=1\text{MHz}$	--	0.85	--	
Q_g	Total Gate Charge	$V_{\text{DS}}=15\text{V}$, $I_{\text{D}}=20\text{A}$, $V_{\text{GS}}=10\text{V}$	--	38	--	nC
Q_{gs}	Gate-Source Charge		--	5.1	--	nC
Q_{gd}	Gate-Drain Charge		--	12	--	nC
Switching Characteristics						
$t_{\text{d}(\text{on})}$	Turn-on Delay Time	$V_{\text{DD}}=15\text{V}$, $I_{\text{D}}=20\text{A}$, $R_g=3$, $V_{\text{GS}}=10\text{V}$	--	8.5	--	nS
t_r	Turn-on Rise Time		--	9	--	nS
$t_{\text{d}(\text{off})}$	Turn-Off Delay Time		--	31	--	nS
t_f	Turn-Off Fall Time		--	9	--	nS
Source- Drain Diode Characteristics						
V_{SD}	Forward on voltage	$I_{\text{SD}}=20\text{A}$, $V_{\text{GS}}=0\text{V}$	--	0.8	1.2	V
t_{rr}	Reverse Recovery Time	$T_j=25^\circ\text{C}$, $I_{\text{SD}}=20\text{A}$, $V_{\text{GS}}=0\text{V}$ $di/dt=500\text{A}/\mu\text{s}$	--	16	--	nS
Q_{rr}	Reverse Recovery Charge		--	42	--	nC

Note:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Limited by T_{Jmax} , starting $T_j = 25^\circ\text{C}$, $L = 0.5\text{mH}$, $R_g = 25$, $I_{\text{AS}} = 15\text{A}$, $V_{\text{GS}} = 10\text{V}$. Part not recommended for use above this value
- ③ Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.



Typical Electrical and Thermal Characteristics(Curves)



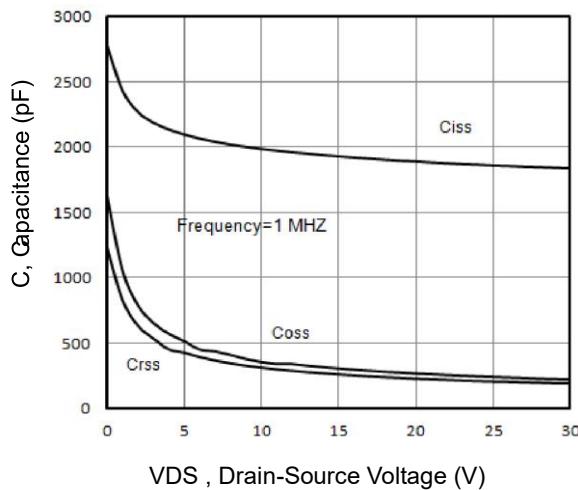


Fig7. Typical Capacitance Vs.Drain-Source Voltage

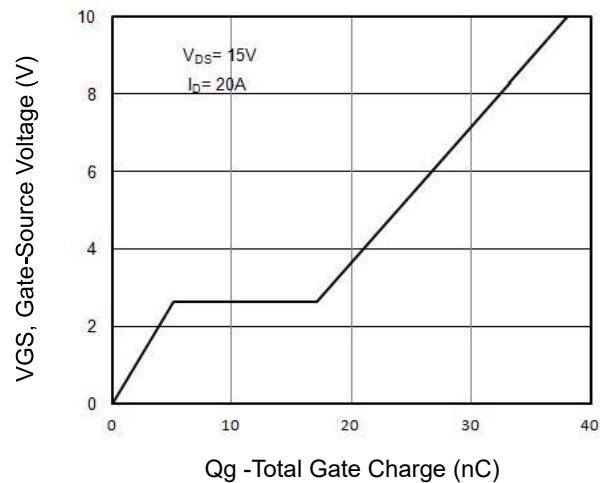


Fig8. Typical Gate Charge Vs.Gate-Source Voltage

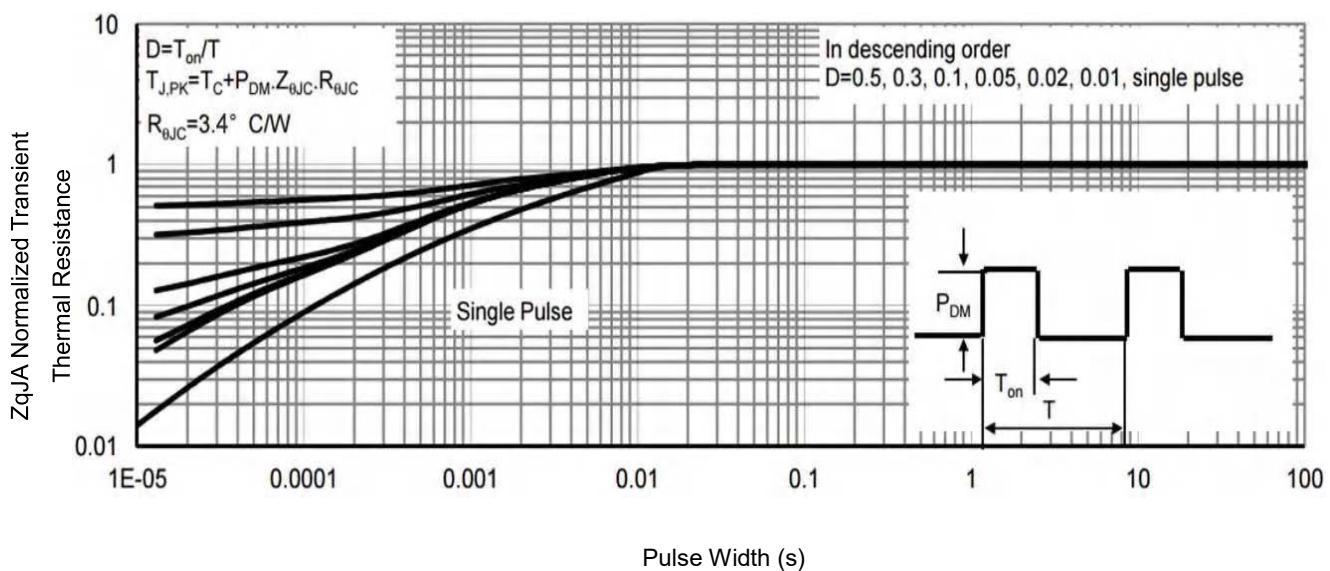


Fig9. Normalized Maximum Transient Thermal Impedance

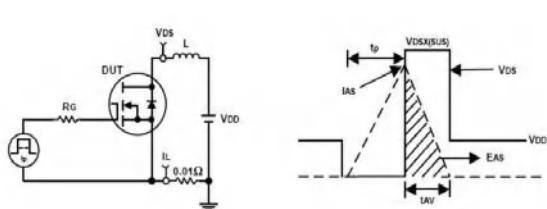


Fig10. Unclamped Inductive Test Circuit and waveforms

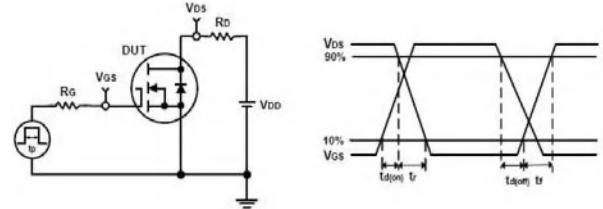
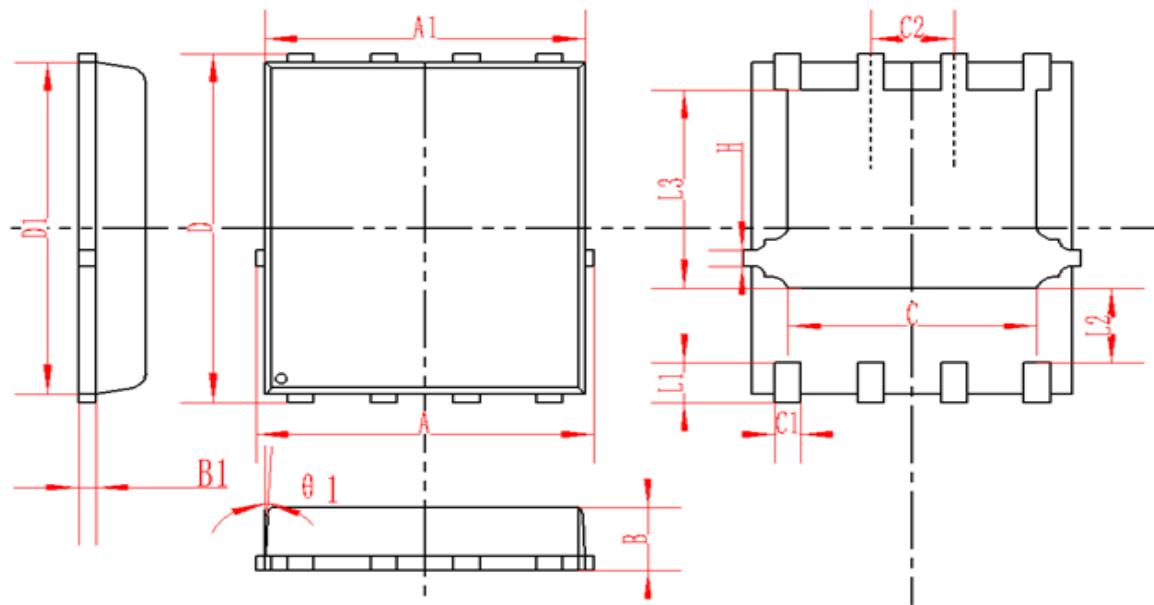


Fig11. Switching Time Test Circuit and waveforms



DFN5X6-8L Package Information



SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.95	5	5.05	0.195	0.197	0.199
A1	4.82	4.9	4.98	0.190	0.193	0.196
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.67	5.75	5.83	0.223	0.226	0.230
B	0.9	0.95	1	0.035	0.037	0.039
B1	0.254REF			0.010REF		
C	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2	1.27TYP			0.5TYP		
θ1	8°	10°	12°	8°	10°	12°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
H	0.24	0.25	0.26	0.009	0.010	0.010



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